

TO-92MOD Plastic-Encapsulated Transistors

2SC2060 TRANSISTOR (NPN)

FEATURE

Power dissipation

$$P_{CM}: 0.75 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

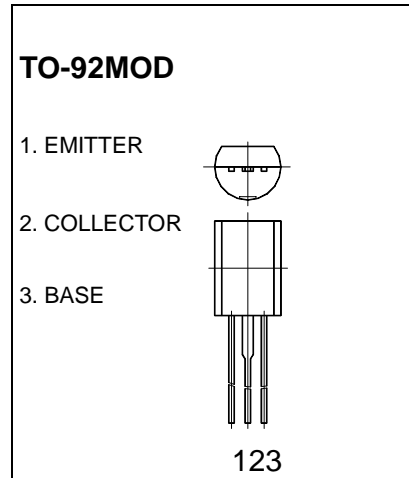
$$I_{CM}: 1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	32		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\text{V}, I_E = 0$		0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 3\text{V}, I_C = 100\text{mA}$	80	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		0.4	V